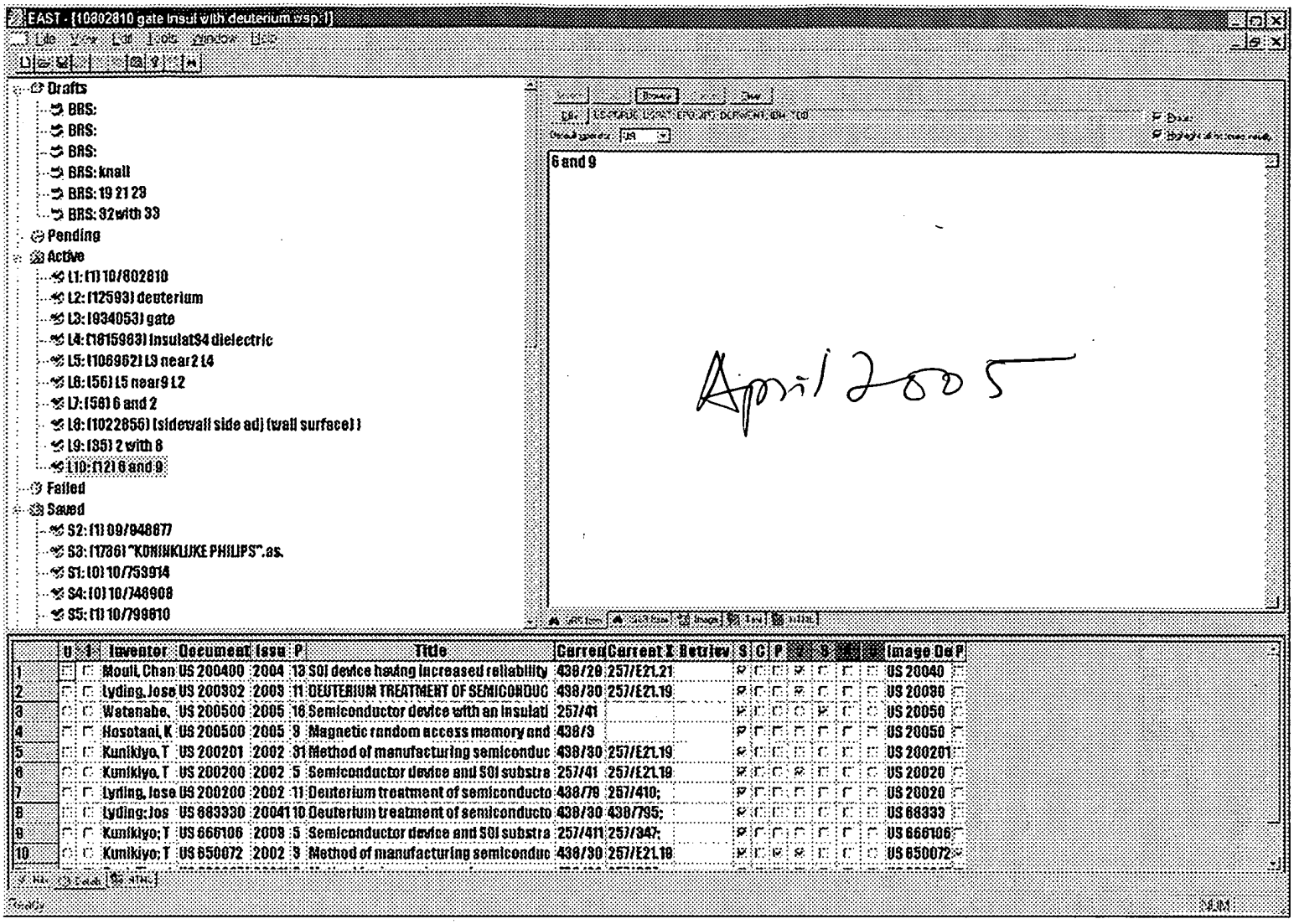
EAST - [10802810 gate insul with deuterium.wsp:1]
File View Edit Tools Window Help
Drafts
BRS:
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BRS: knall
BRS: 19 21 29
BRS: 32 with 33
Pending
Active
L1: (1) 10/802810
L2: (12593) deuterium
L3: (934053) gate
L4: (1815983) insulat$4 dielectric
L5: (106962) L3 near2 L4
L6: (56) L5 near9 L2
L7: (56) 6 and 2
L8: (1022656) (sidewall side adj (wall surface))
L9: (35) 2 with 8
L10: (12) 6 and 9
Failed
Saved
S2: (1) 09/948677
S3: (1736) "KONINKLIJKE PHILIPS".as.
S1: (0) 10/753914
S4: (0) 10/748908
S5: (1) 10/799610
6 and 9
April 2005
U 1 Inventor Document Issu P Title Current Current X Retriev S C P 8 9 Image De P
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2 Lyding, Jose US 200302 2003 11 DEUTERIUM TREATMENT OF SEMICONDUC 438/30 257/E21.19 US 20030
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